



# DC Link Capacitor and Wireless Power Transfer A Perfect Couple?!



APEC 2020 in New Orleans  
Capacitor Workshop PSMA



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eICap / eIRis Capacitors & Resistors Division

# Introduction of the Presenter



## Frank Puhane

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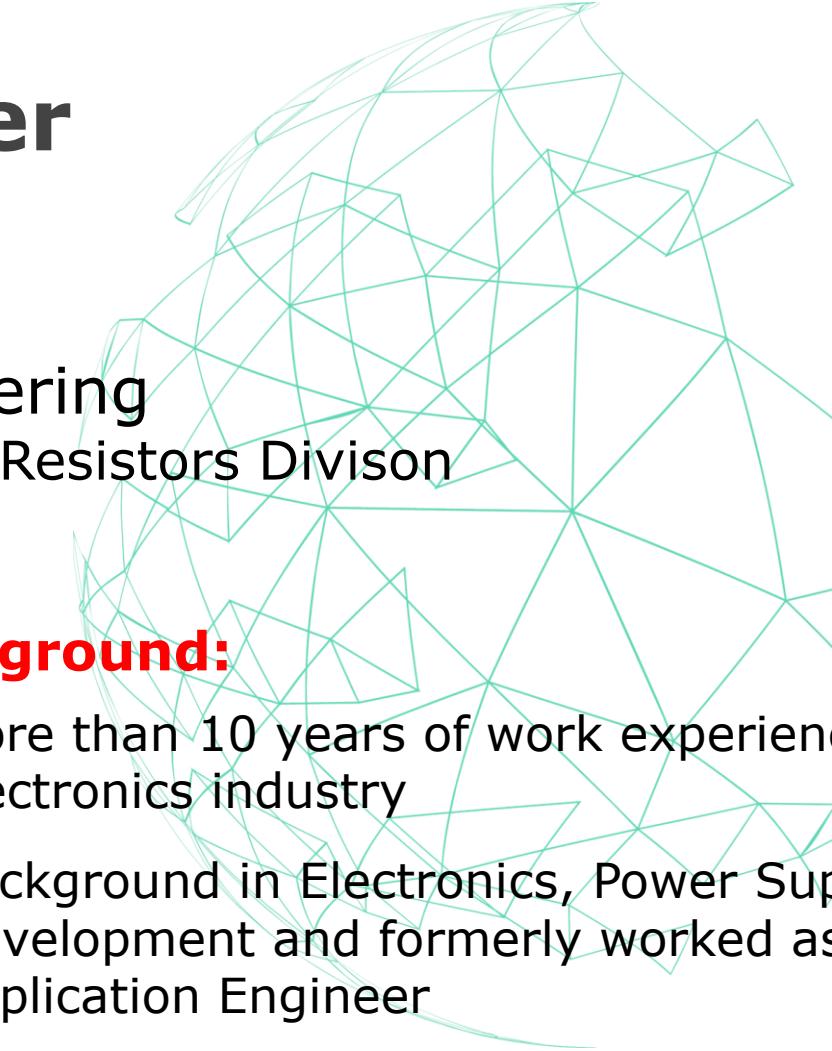


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### Background:

- More than 10 years of work experience in electronics industry
- Background in Electronics, Power Supply Development and formerly worked as Field Application Engineer
- In charge for technical engineering, product services and application support of capacitor division at Würth Elektronik



# Agenda

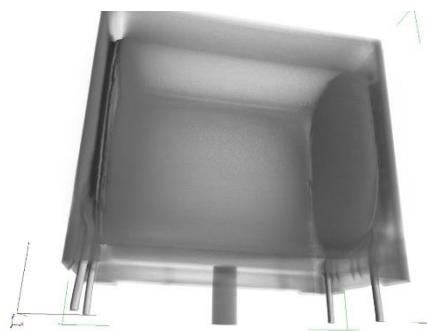
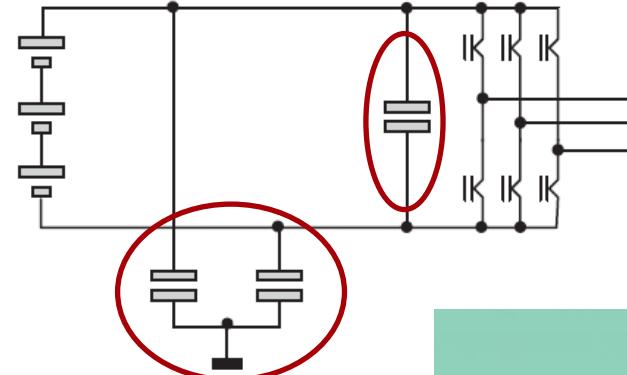
- Why and What is a DC Link Capacitor?
- Differences to other Technologies
- Example of Capacitance Calculation
- 11kW Wireless Power Transfer System
- Further Possibilities



# Why and What is a DC Link Capacitor?



- **Essential stage in power conversion**
- **Applications like:**
  - Three-phase inverters
  - Photovoltaic and wind power inverters
  - Industrial motor drives
  - Automotive onboard chargers and inverters
  - Medical equipment power supplies
- **They stabilize the DC Link voltage**
- **Withstand high RMS currents**
  - Design DC Link capacitor on RMS current value

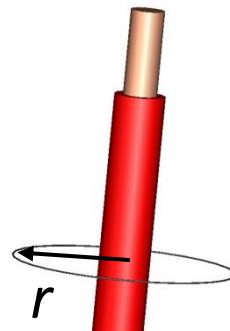


# Why and What is a DC Link Capacitor?

- DC Link capacitors are used to absorb voltage peaks
- These peaks are generated due to the inductance of the input wire

- The inductance of a wire can be calculated with the following formula

$$L = \left[ \frac{\mu_0 * \mu_{Copper}}{8 * \pi} \right] * I$$



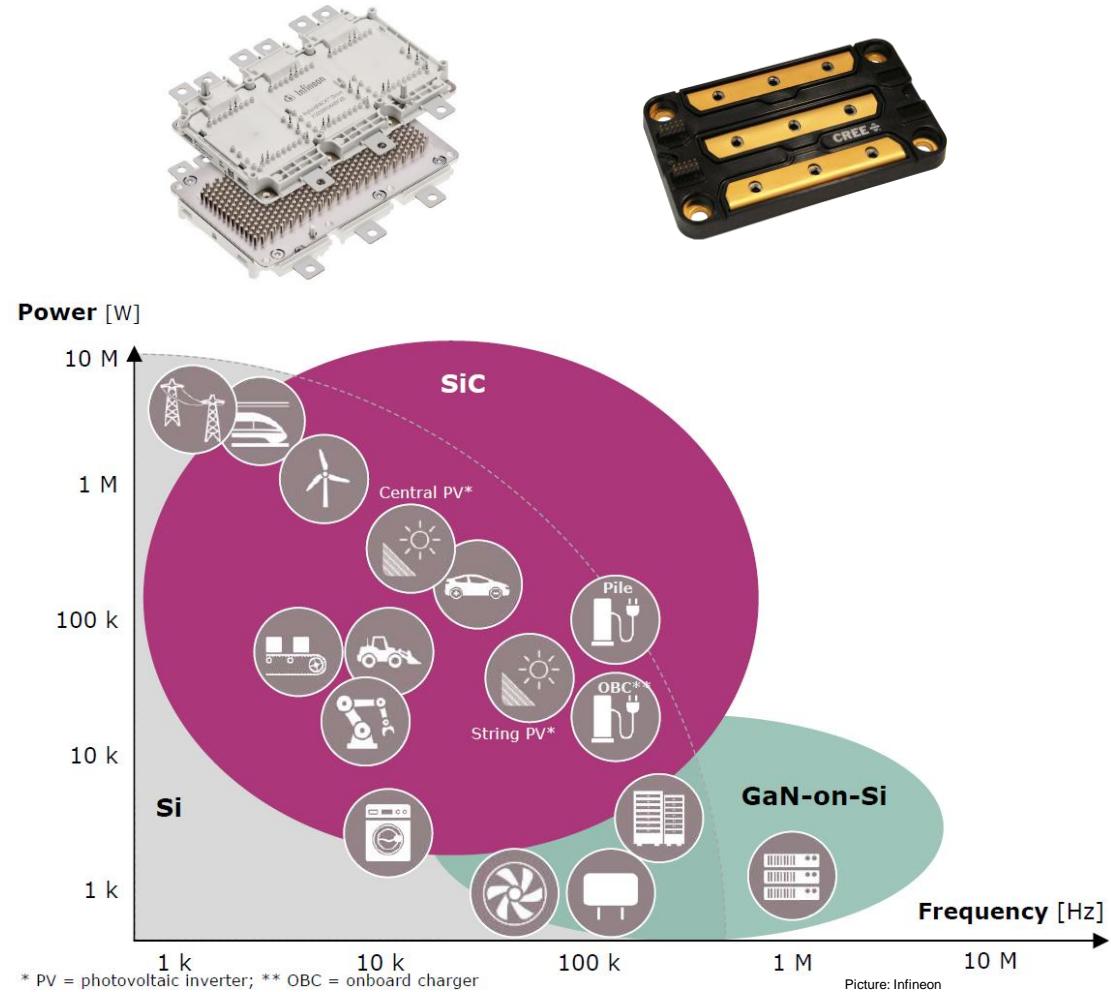
$$H = \frac{l}{2 \cdot \pi \cdot r}$$

- So for a 1m wire the inductance will be 50nH.
- Depending on the calculated inductance of the wire, there will be limitation of the recommended length of the wire in the system
- DC-Link capacitor < 1 nH per mm of lead spacing

# DC Link Capacitor and SiC Modules



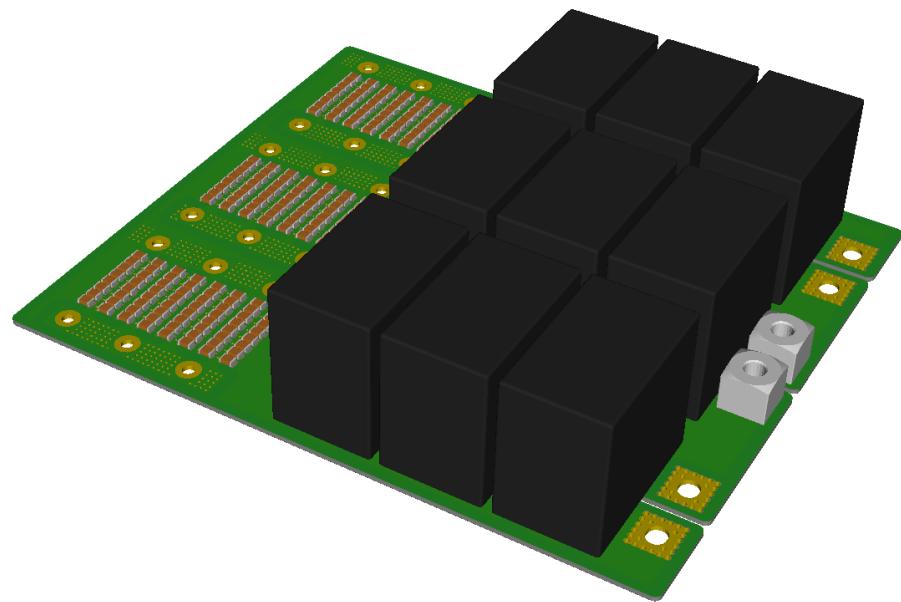
- **SiC technology has some key points:**
  - Very high switching voltages
  - High switching frequency possible
  - Low losses in the semiconductor
  - 15kV/μsec are typical values for silicon carbide
  
- **There are different vendor for silicon carbide**
  - Cree, Infineon, Rohm and so on



# DC Link Capacitor and SiC Modules



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# Film vs. Aluminum DC Link Technology

## Film DC Link Capacitor

- **High RMS current capabilities**
  - Up to 1 A<sub>RMS</sub> per  $\mu\text{F}$
- **Over voltage withstand**
  - Up to 2 times the rated voltage
- **Handle voltage reversal**
- **No acid inside**
- **Long lifetime / no storage problem**
- **Good temperature cooling system possible**
- **Self-healing properties**

## Aluminum Electrolytic DC Link Capacitor

- **High capacitance values**
  - Going up to 4700  $\mu\text{F}$
- **RMS current capabilities**
  - Depends on the part 1 mA...20 mA or higher
- **Rated voltages up to 650 V**
  - R&D is ongoing
  - Cascade assembly to reach the desired voltage level



Picture: Freepik.com

# Film vs. Aluminum DC Link Technology

Property	Film Capacitor	Aluminum Electrolytic Capacitor
<b>Capacitance</b>	low	high
<b>Voltage</b>	up to 1,300 V <sub>DC</sub>	actually 650V <sub>DC</sub>
<b>Lifetime</b>	approx. 100,000 hours	10,000 - 20,000 hours (probably longer with higher C - derating >20%)
<b>ESR</b>	low	high
<b>Ripple Current Capabilities</b>	High	Low (possibly increased with additional cooling)
<b>Energy density</b>	<0.2 J/cm <sup>3</sup>	about 0.82 J/cm <sup>3</sup>

- The replacement microfarad for microfarad will not work
- Replacement won't be possible for each application

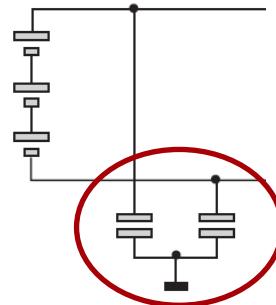
# How to Calculate the Capacitance?



## Bypass application

- Film Capacitor
- Working voltage: 240 V<sub>DC</sub>
- Ripple voltage max: 5 V<sub>RMS</sub>
- RMS current: 50 A<sub>RMS</sub> @ 15 kHz
- Needed capacitance value:

$$\text{▪ } C = \frac{I_{rms}}{V_{ripple} \cdot 2 \cdot \pi \cdot f} = \frac{50A}{5V \cdot 2 \cdot \pi \cdot 15kHz} = 106\mu F$$



- Aluminum Electrolytic capacitor
- RMS current capability 10 mA per  $\mu F$
- Have to handle the 50 A<sub>rms</sub>
- Needed capacitance value:

$$\text{▪ } C = \frac{I_{rms}}{\text{Max I per } \mu F} = \frac{50A}{0.01A} * 1\mu F = 5000\mu F$$



# How to Calculate the Capacitance?

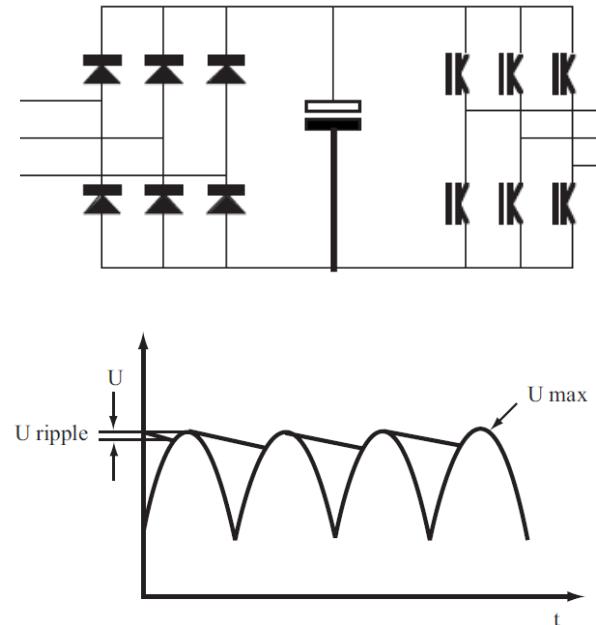


## Energy Storage

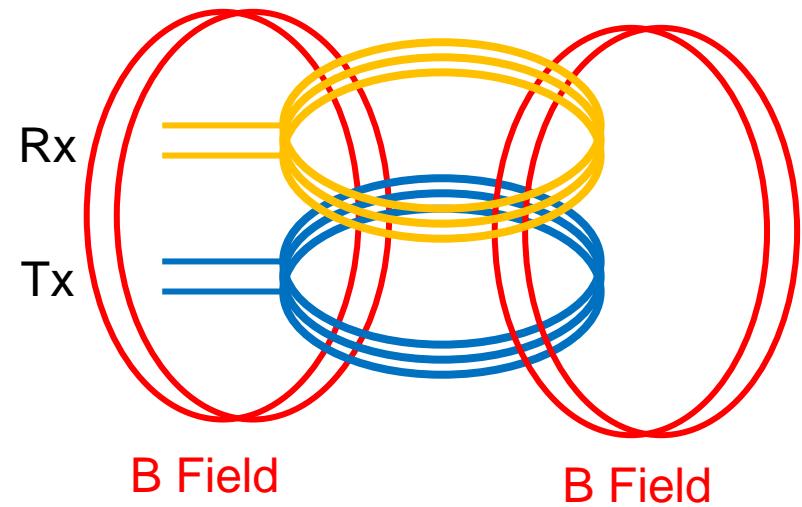
- Supply frequency is lower than converter frequency
- $$C = \frac{P_{load}}{V_{ripple} \cdot \left[ V_{max} - \frac{V_{ripple}}{2} \right] \cdot F_{rectifier}}$$
- $I_{RMS}$  approximation depends on the power of load,  $V_{max}$  and  $V_{ripple}$
- $$I_{rms} = \frac{V_{ripple}}{2 \cdot \sqrt{2}} \cdot C \cdot 2 \cdot \pi \cdot F_{rectifier}$$
- $$I_{rms} = \frac{P_{load} \cdot \pi}{\left[ V_{max} - \frac{V_{ripple}}{2} \right] \cdot \sqrt{2}}$$

### Example:

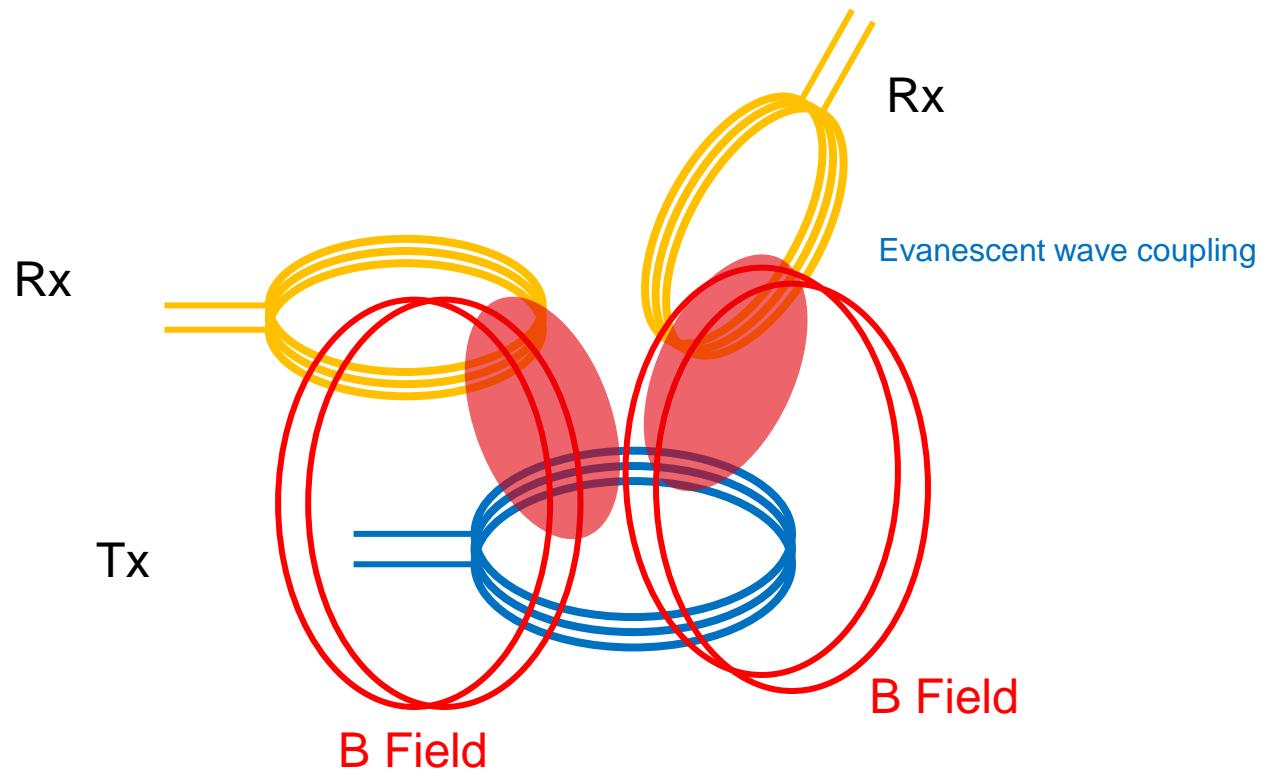
- $P_{load} = 10 \text{ kW}$
- $V_{max} = 800 \text{ V}$
- $V_{ripple} = 100 \text{ V}$
- Film Technology
  - $C = 444 \mu\text{F}$
  - $I_{rms} = 29.6 \text{ A}$
- Aluminum Technology
  - With 20 mA<sub>rms</sub> per  $\mu\text{F}$
  - $C = 1480 \mu\text{F}$



# Wireless Power Transfer System

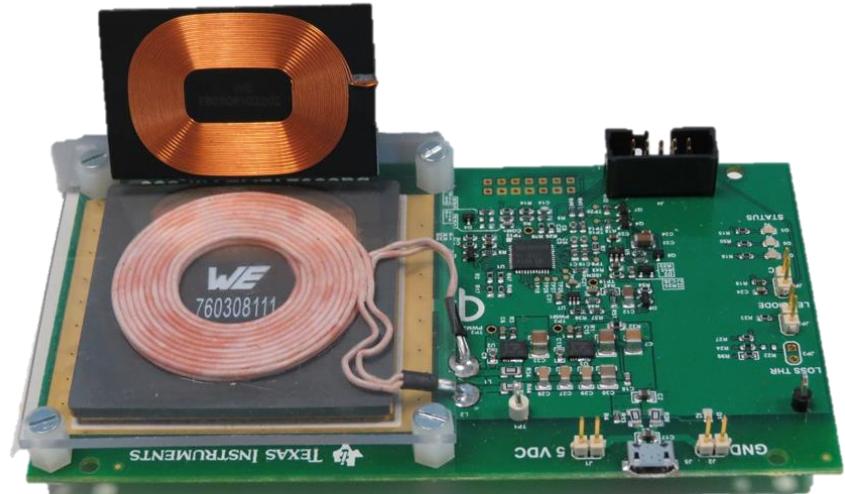


**Inductive Power Transfer**

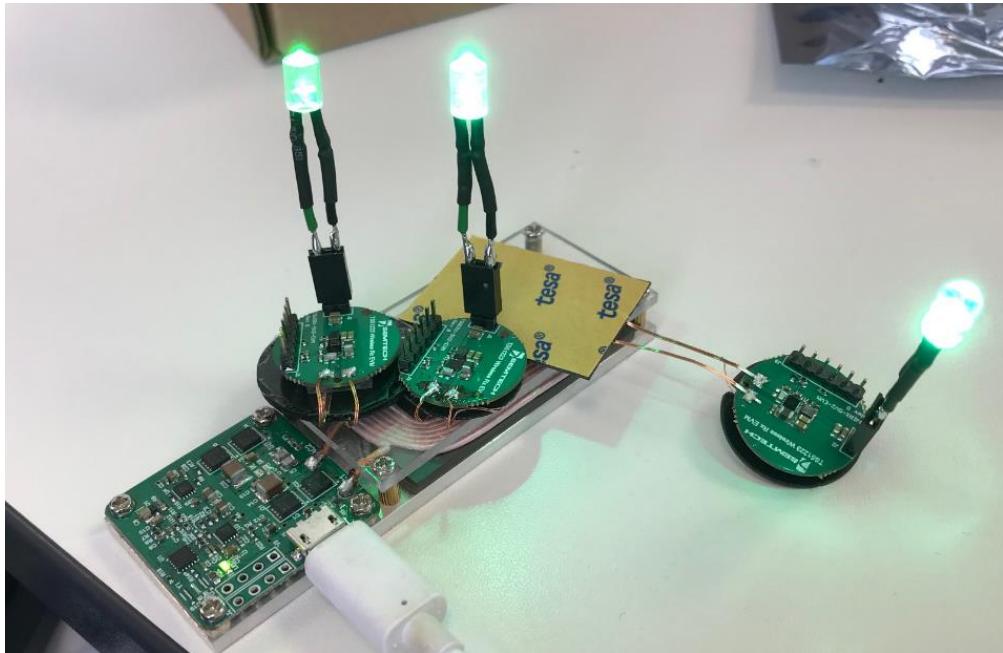


**Resonant Power Transfer**

# Wireless Power Transfer System



**Inductive Power Transfer**

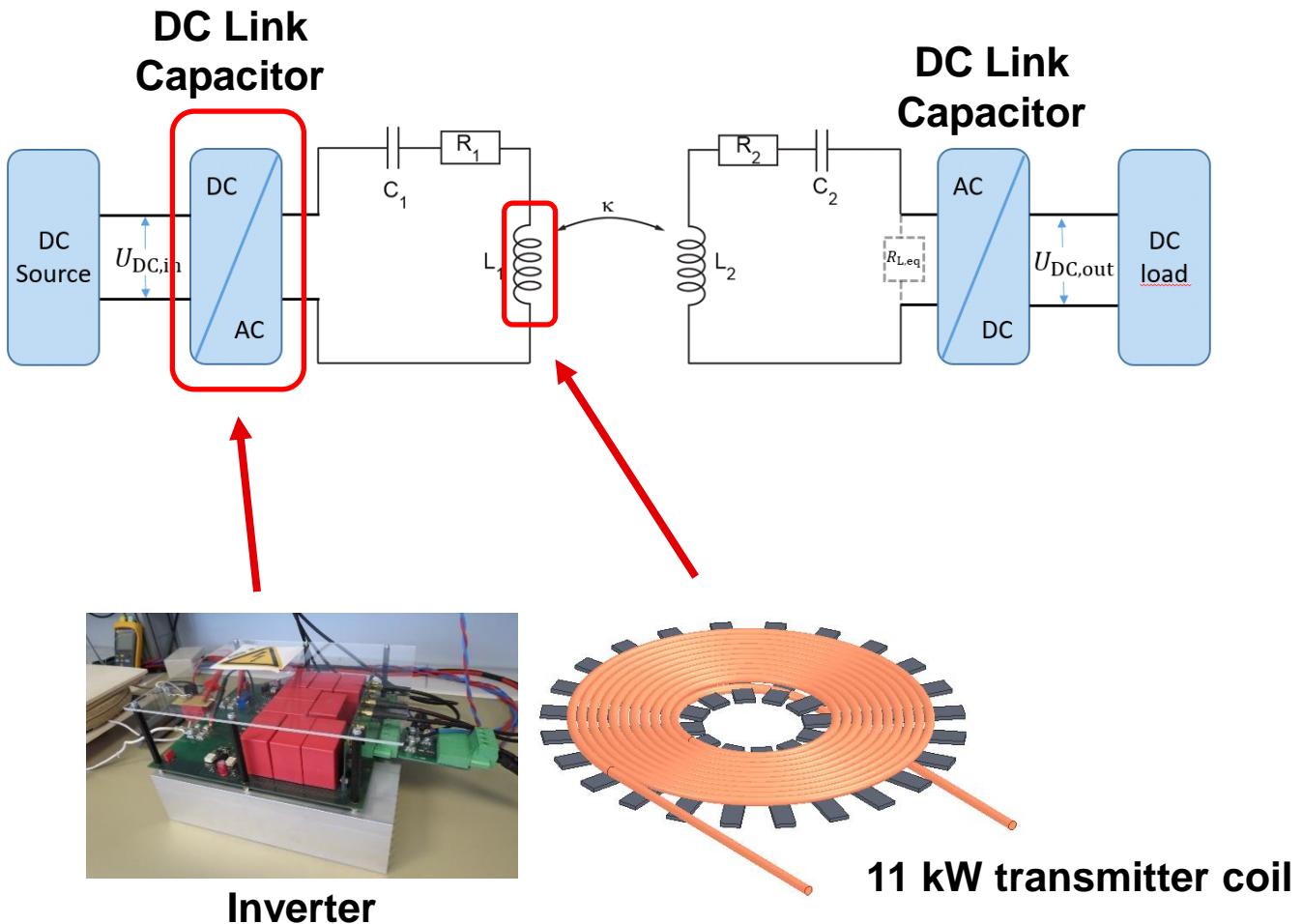


**Resonant Power Transfer**

# 11kW Wireless Power Transfer System



- Specification of the system:
- $P_{out} = 11 \text{ kW}$
- $V_{DC} \approx 370 \text{ V}$
- $I_{RMS} \approx 30 \text{ A}$
- $V_{\text{ripple}} = 0.2 \text{ V}$
- DC to DC efficiency  $\approx 98 \%$



Source: Würth Elektronik eiSos Wireless Power Transfer Division, Christoph Utschick

# 11kW Wireless Power Transfer System

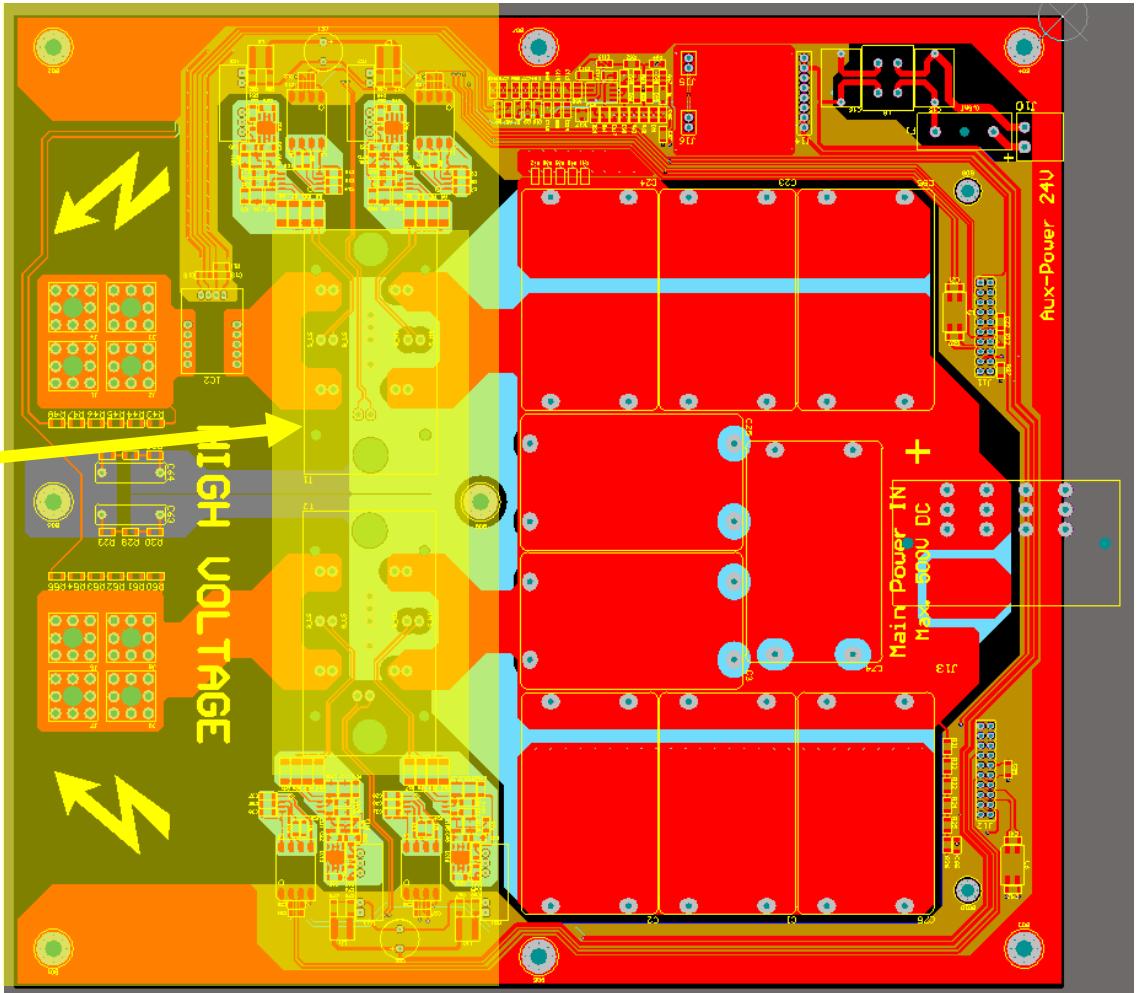


## Key points of the design:

- Symmetrical construction
- High-Side / Low-Side Gate Control
- Two SiC Modules
  - FF23MR12W1M1B11BOMA1
  - Dual CoolSiC™ MOSFET
  - $V_{DSS} = 1200 \text{ V}$
  - $I_{D\_nom} = 50 \text{ A}$
  - $I_{D\_pulse} = 100 \text{ A}$
  - $f_{switch} = 100 \text{ kHz...200 kHz}$



Source: Würth Elektronik eiSos Wireless Power Transfer Division, Cem Som



# 11kW Wireless Power Transfer System

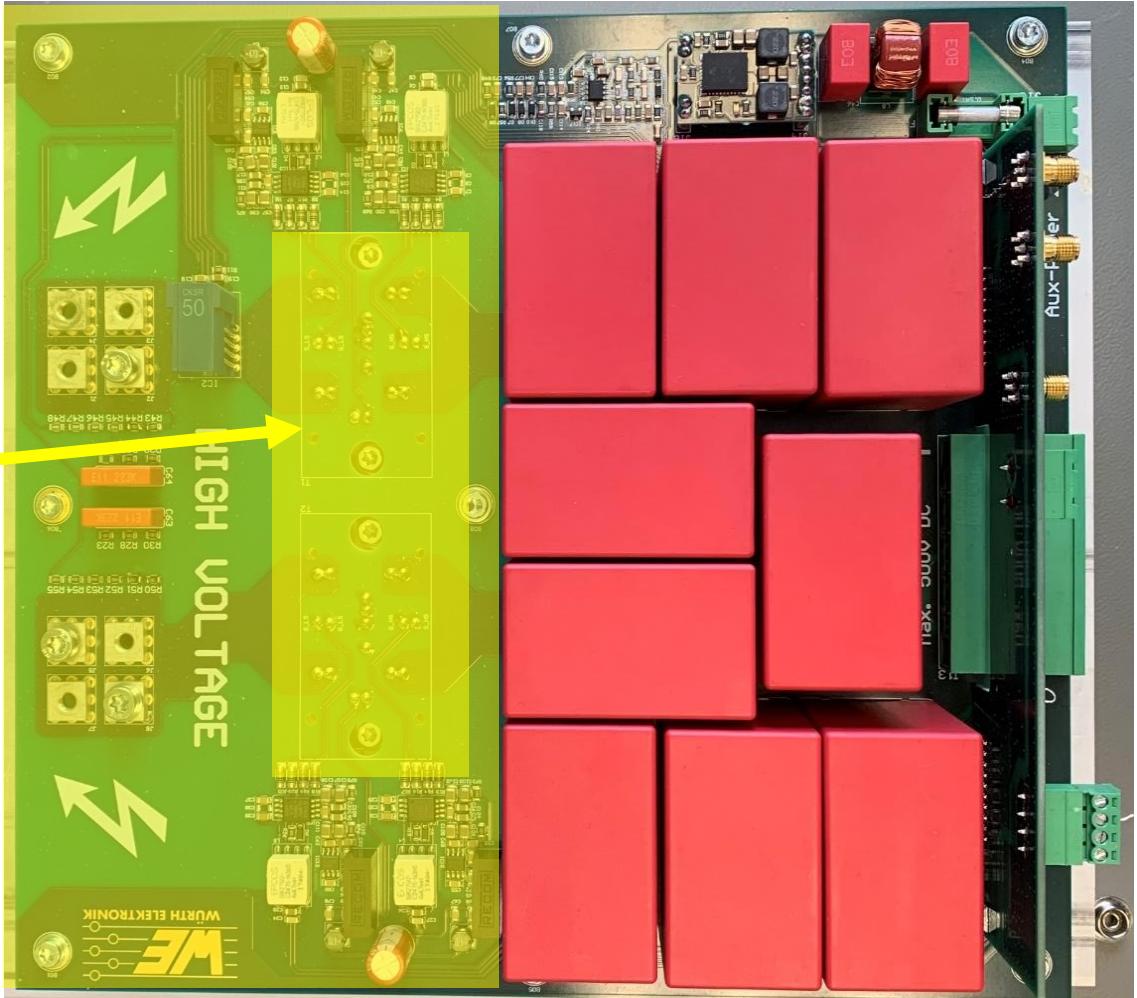


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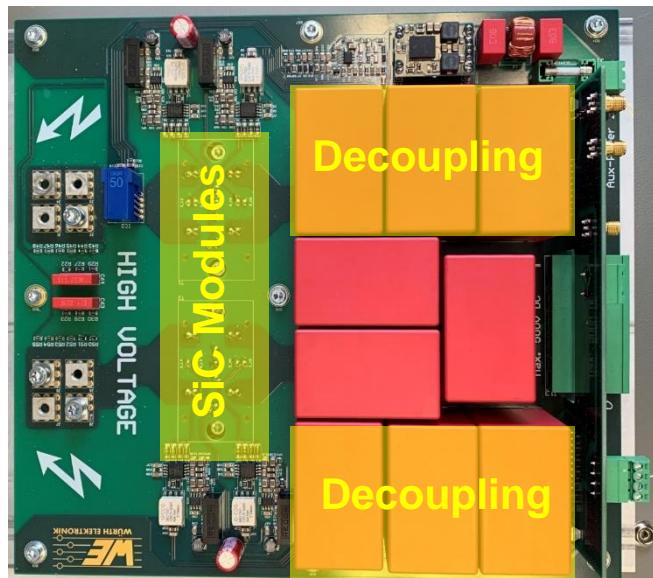


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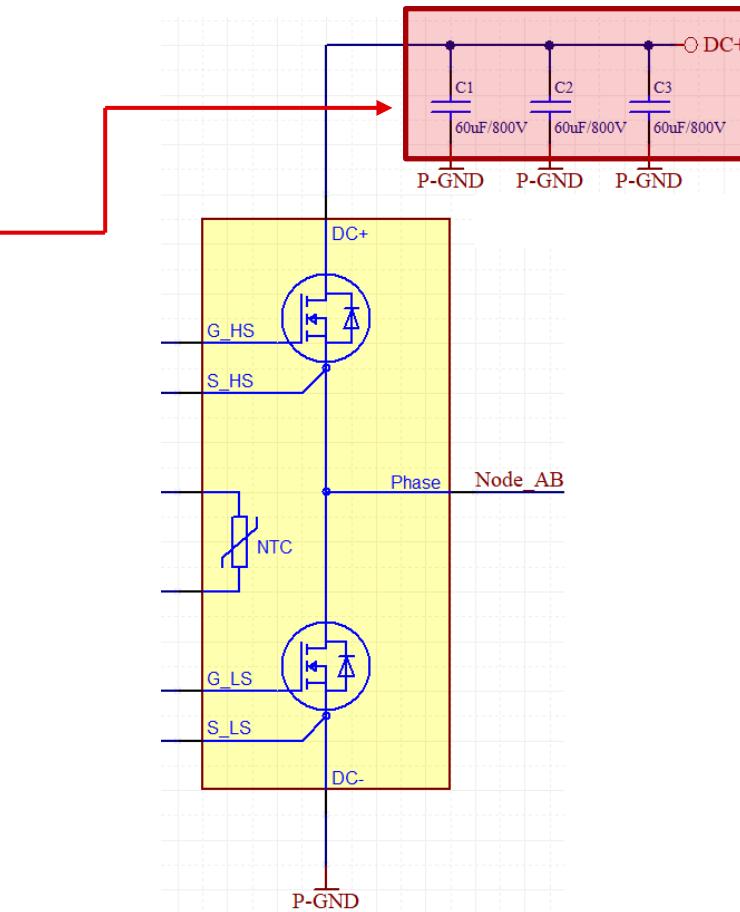
## Calculation of the capacitance values:

- Decoupling for the SiC Modules

$$C = \frac{I_{rms}}{V_{ripple} \cdot 2 \cdot \pi \cdot f} = \frac{30A}{0.2V \cdot 2 \cdot \pi \cdot 150kHz} = 160\mu F$$



Source: Würth Elektronik eiSos Wireless Power Transfer Division, Cem Som



## Specification:

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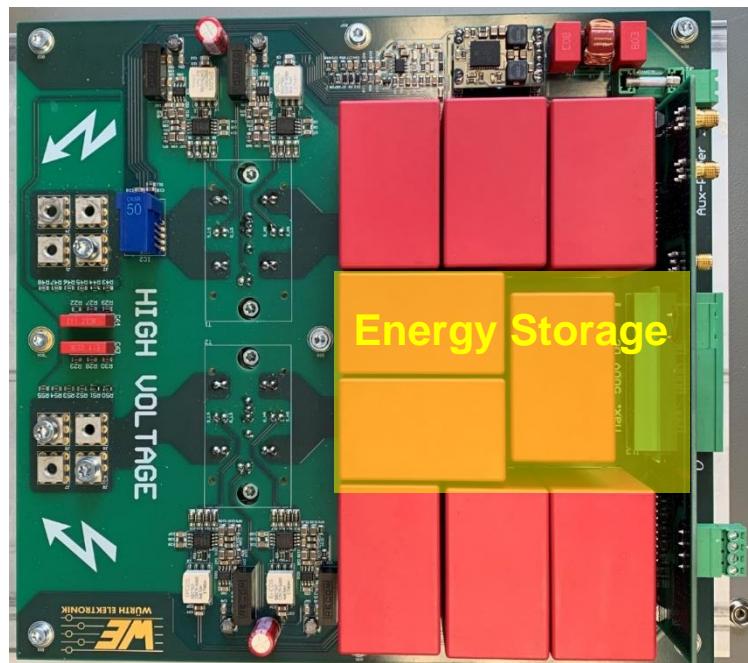
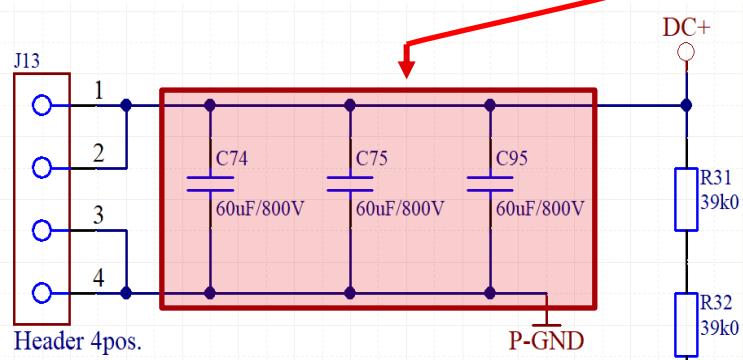


## Calculation of the capacitance values:

- **Energy Storage for  $V_{DC}$**

$$C = \frac{P_{load}}{V_{ripple} \cdot \left[ V_{max} - \frac{V_{ripple}}{2} \right]} = 150\mu F$$

$$I_{rms} = \frac{P_{load} \cdot \pi}{\left[ V_{max} - \frac{V_{ripple}}{2} \right] \cdot \sqrt{2}} = 61A$$



Source: Würth Elektronik eiSos Wireless Power Transfer Division, Cem Som

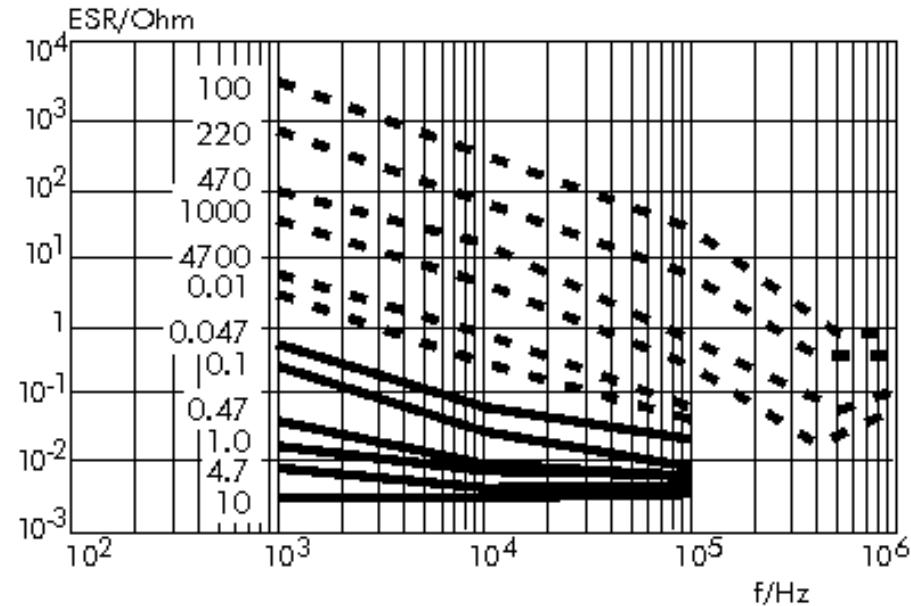
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# 11kW Wireless Power Transfer System



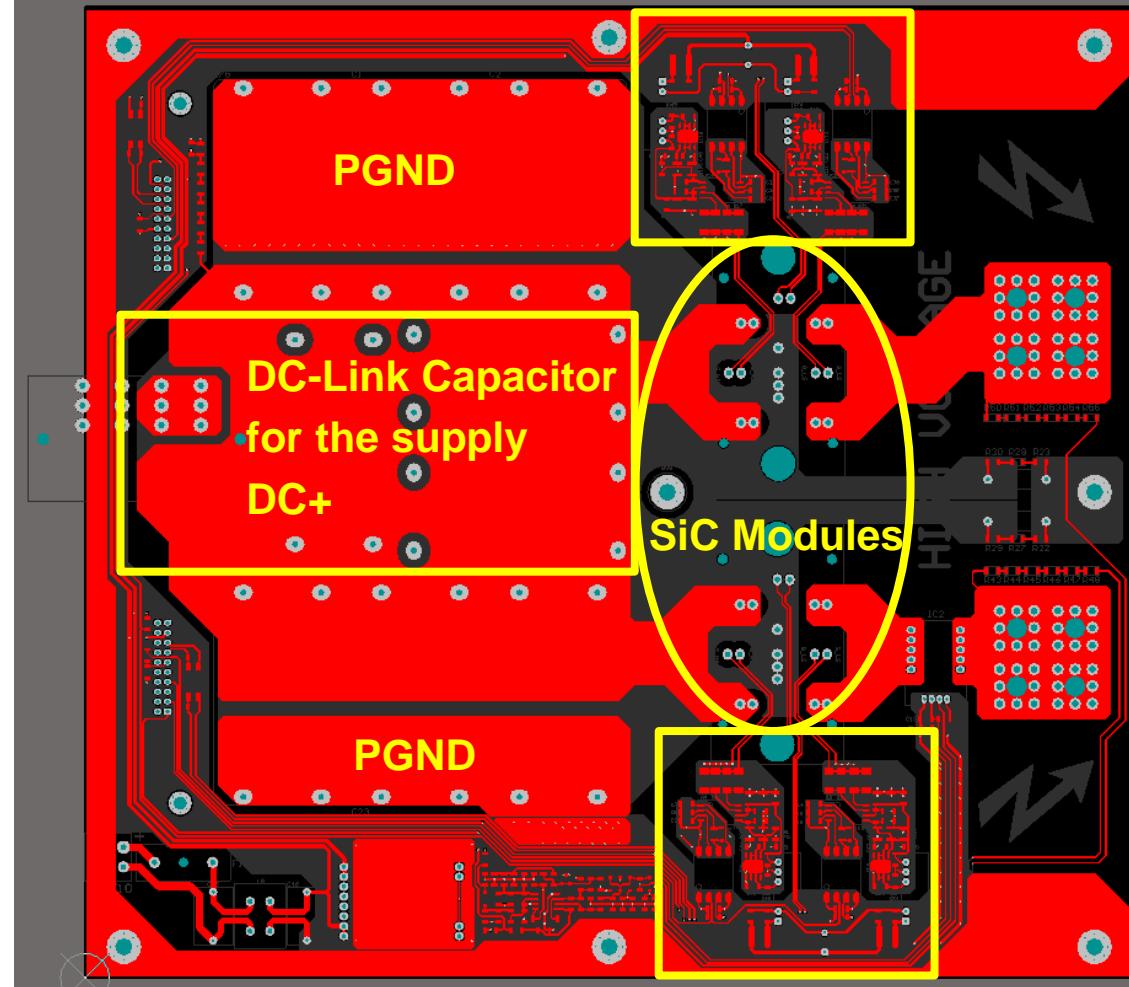
- **DC Link capacitor in film technology**
  - Capacitance = 60  $\mu\text{F}$
  - Rated voltage = 800 V
  - Low ESR = 2.9 mR
  - RMS current = 21.5 A
  - Impulse voltage capability = 15V/ $\mu\text{s}$
  - Easy to achieve in the needed voltage rating > 500 V
- **Decoupling capacitance => 160  $\mu\text{F} / 30 \text{ A}_{\text{rms}}$** 
  - $3 * 60 \mu\text{F} = 180 \mu\text{F}$
  - $3 * 21.5 \text{ A} = 64.5 \text{ A}$
- **Energy storage capacitance => 150 $\mu\text{F} / 61 \text{ A}_{\text{rms}}$** 
  - $3 * 60 \mu\text{F} = 180 \mu\text{F}$
  - $3 * 21.5 \text{ A} = 64.5 \text{ A}$



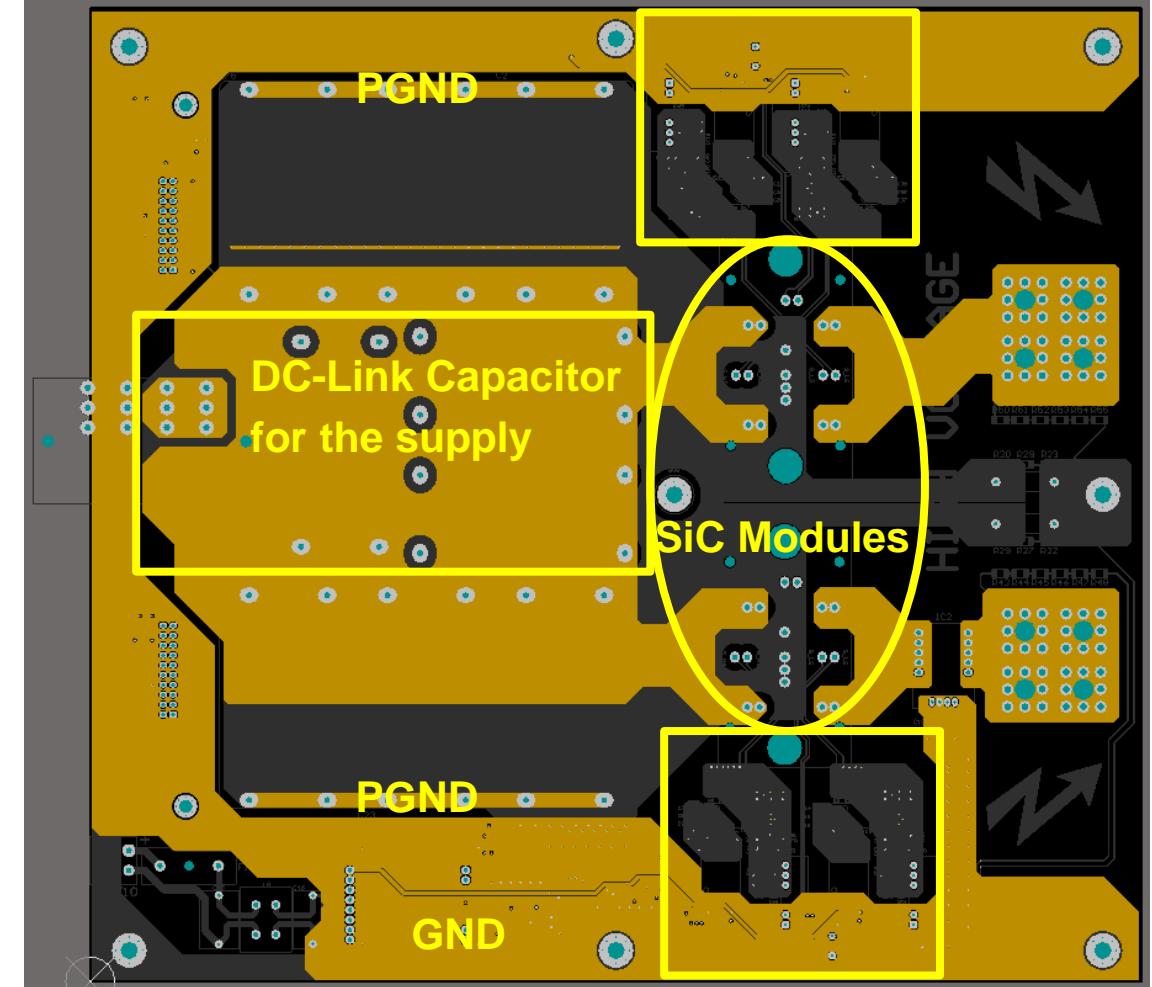
# 11kW Wireless Power Transfer System



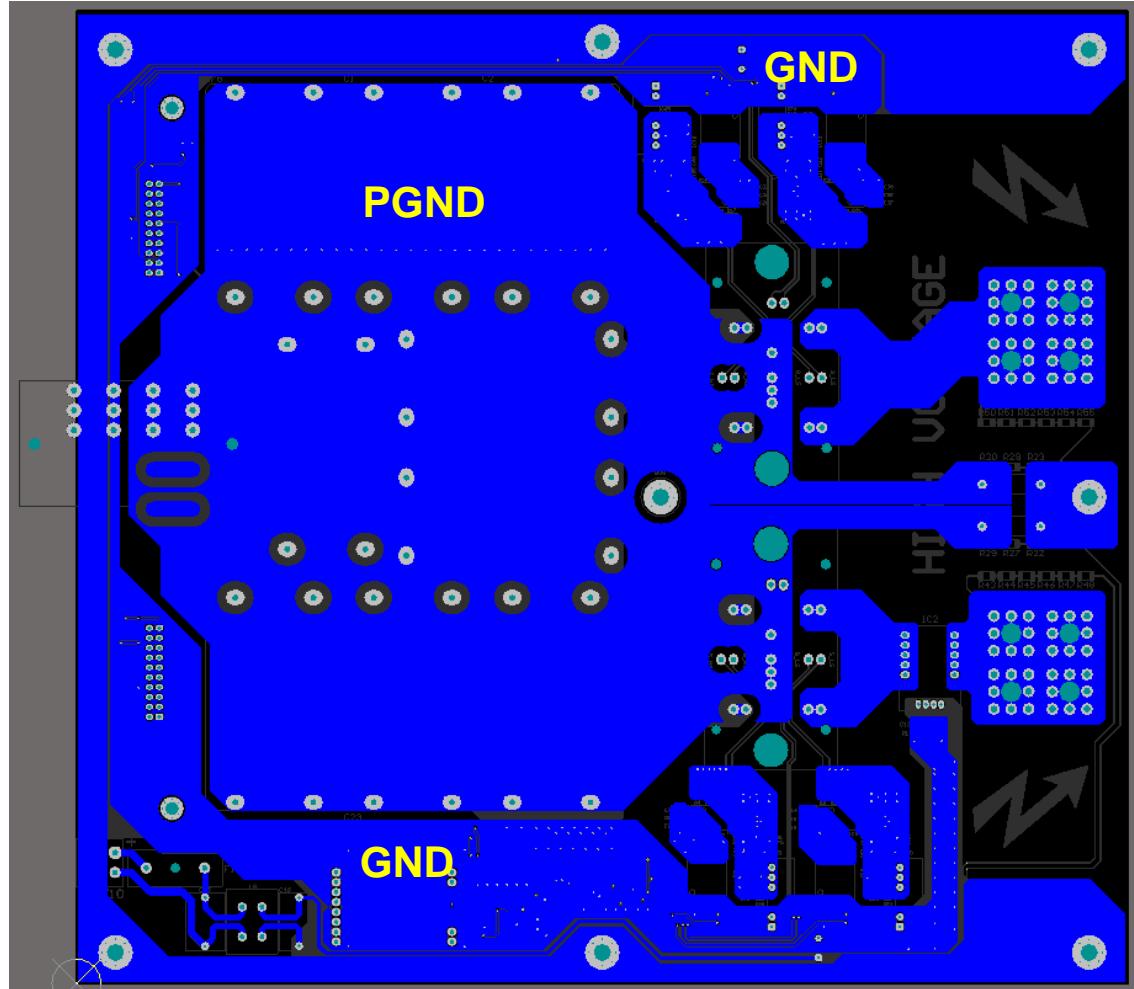
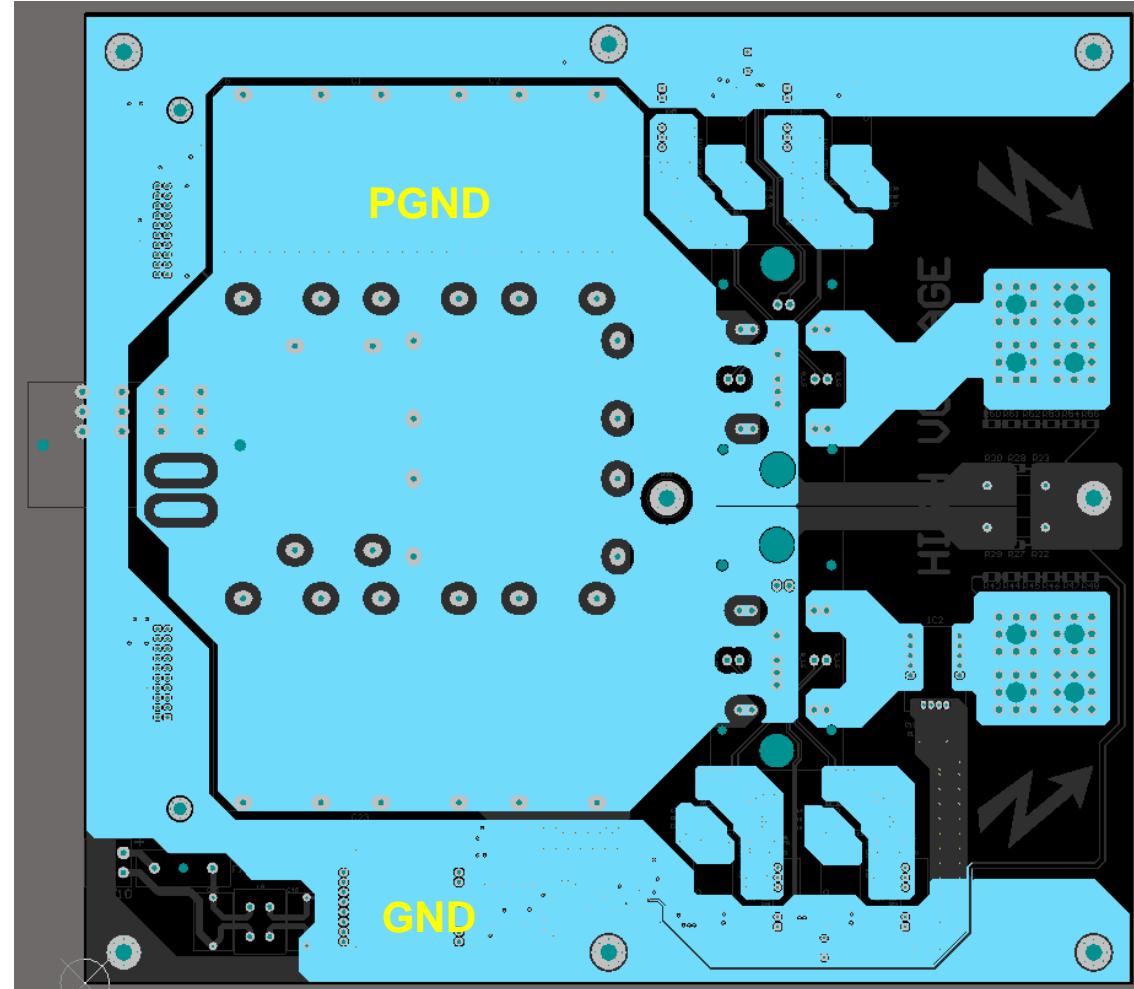
Gate Driver



Gate Driver



# 11kW Wireless Power Transfer System



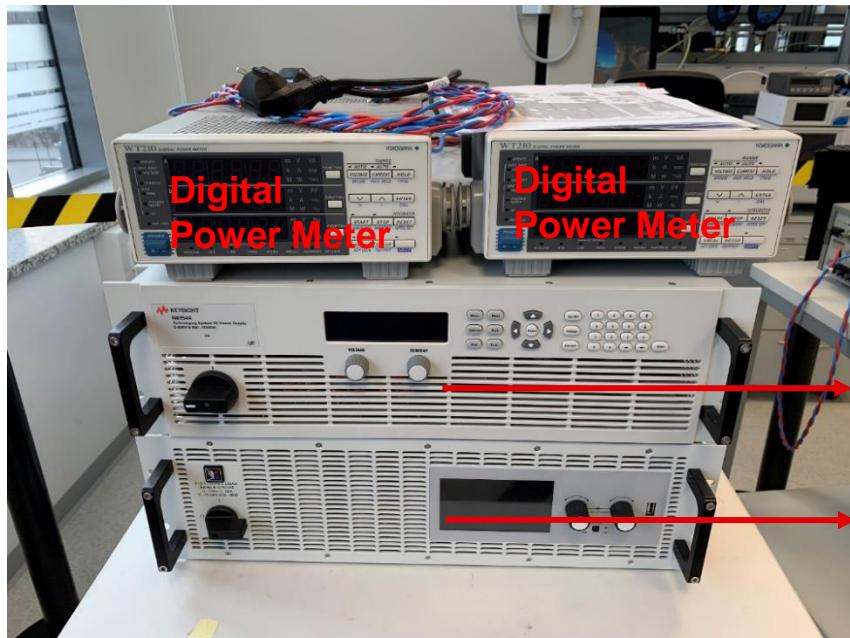
Source: Würth Elektronik eiSos Wireless Power Transfer Division, Cem Som

# Test Setup of the 11kW WPT System



## Specification:

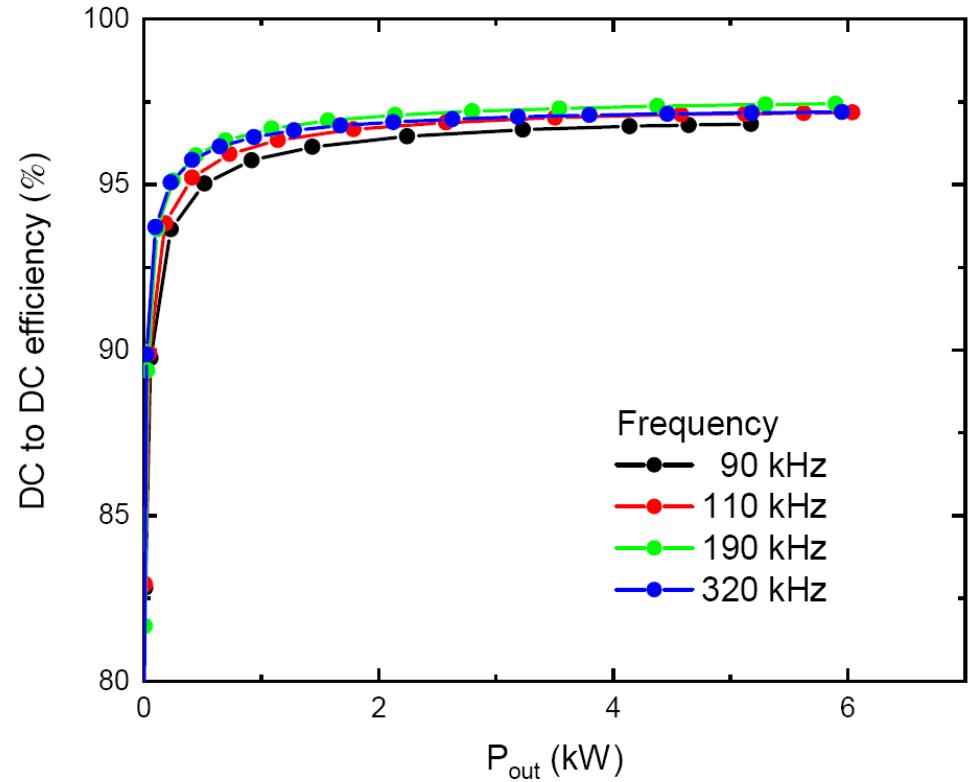
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**DC Power Supply**  
15 kW / 500 V / 90 A

**Electronic Load**  
11 kW / 750 V max.

**Characteristic Full System Efficiency Curve**  
**DC to DC efficiency  $\approx 98 \%$**

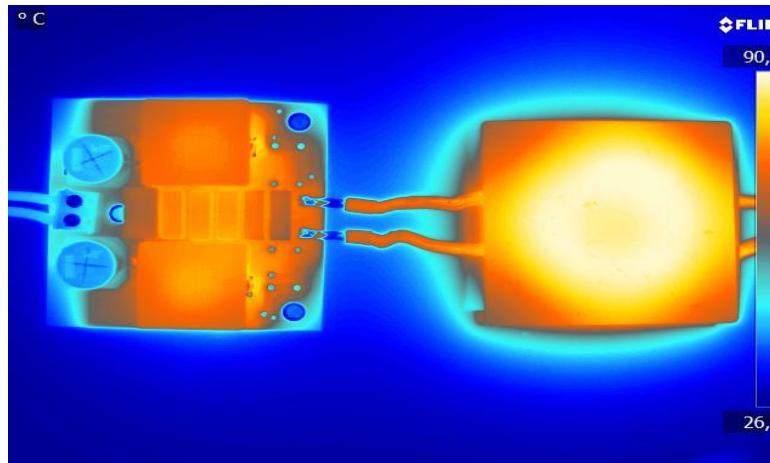
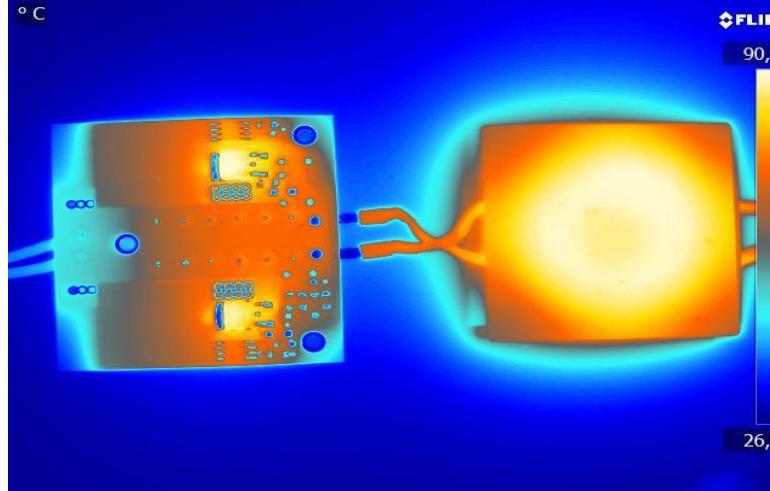


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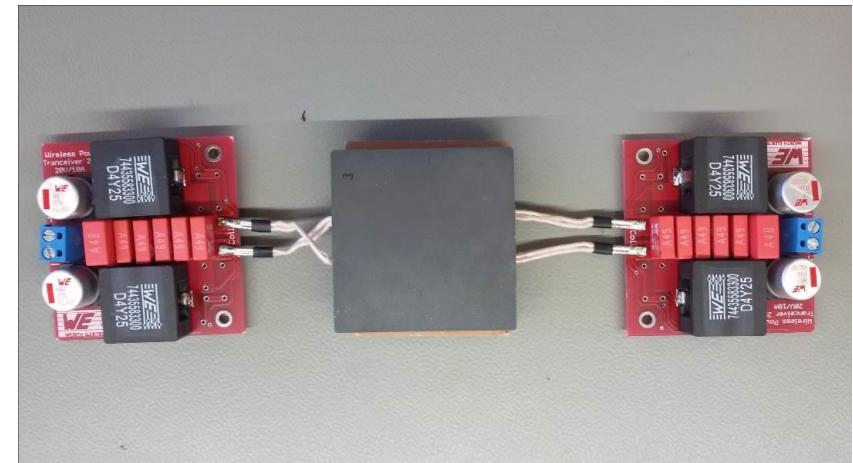
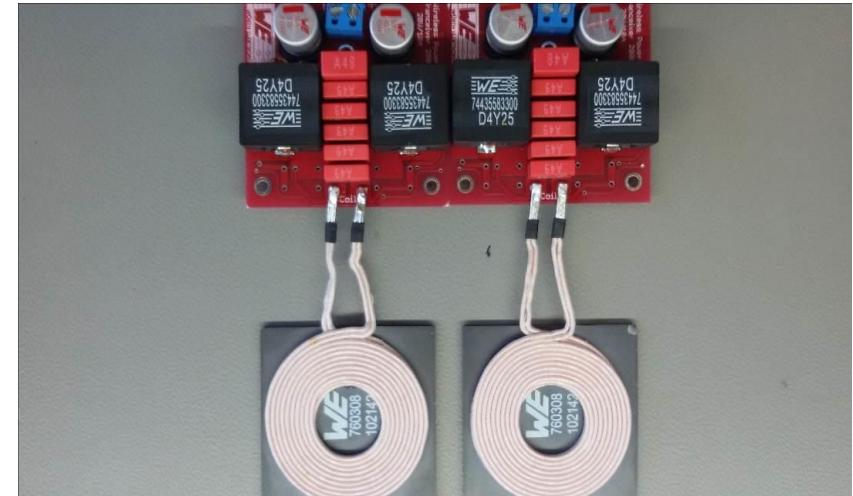
# Wireless Power Transfer 100W



- **Resonant converter**
  - Scalable
  
- **Using film X2 capacitor for the resonant circuit**
  
- **Using aluminum electrolytic capacitor for buffering**
  
- **Simple discrete solution**
  - No micro controller
  - No software



Source: Würth Elektronik eiSos Andreas Nadler



# Questions?



## Thanks for your attention!

